

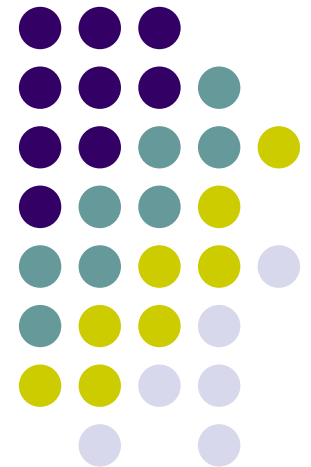
Fine Pixel CCD R&D in Japan

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@Snowmass05



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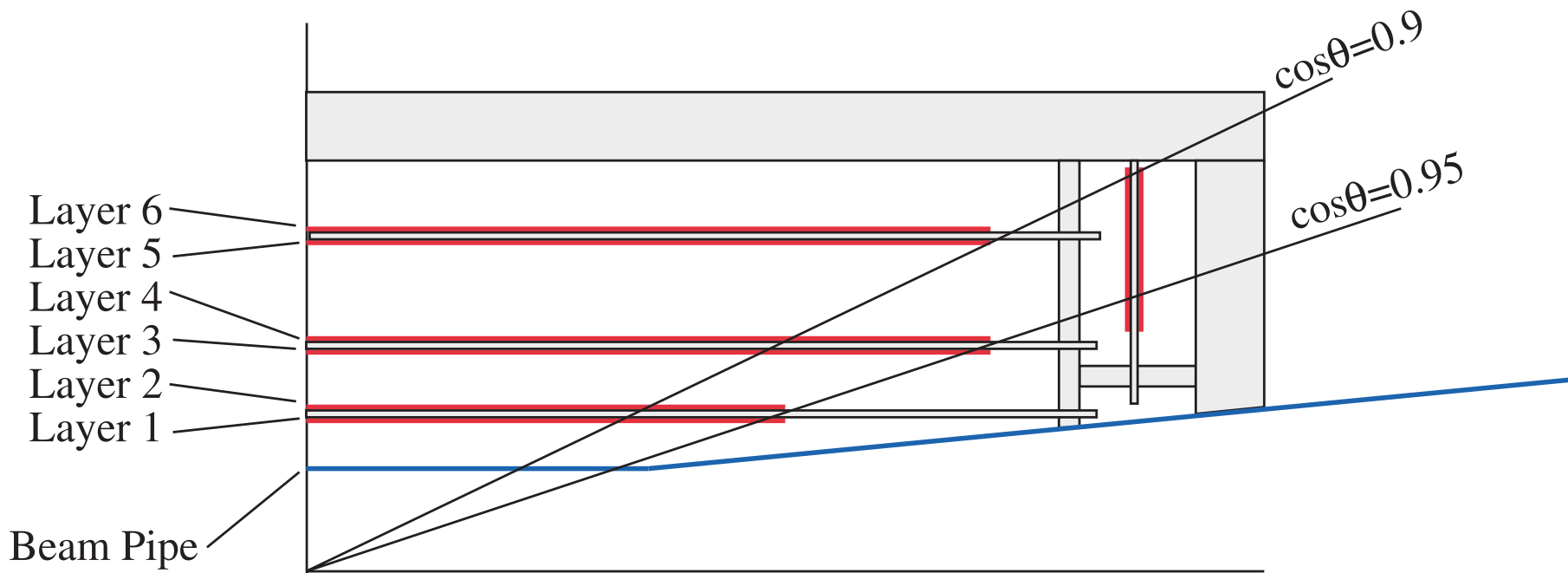
Introduction



- FPCCD Vertex Detector
 - Accumulate hit signals for one train and read out between trains → Completely free from EMI
 - Fine pixel of $\sim 5\mu\text{m}$ (x20 more pixels than “standard” pixels) to keep low pixel occupancy
 - Fully depleted epitaxial layer to minimize the number of hit pixels due to charge spread by diffusion
 - Two layers in proximity make a doublet (super layer) to minimize the wrong-tracking probability due to multiple scattering
 - Tracking capability with single layer using cluster shape can help background rejection
 - Three doublets (6 CCD layers) make the detector
 - Multi-port readout with moderate ($\sim 15\text{MHz}$) speed
 - Operation at low temperature to keep dark current negligible (r.o. cycle=200ms)



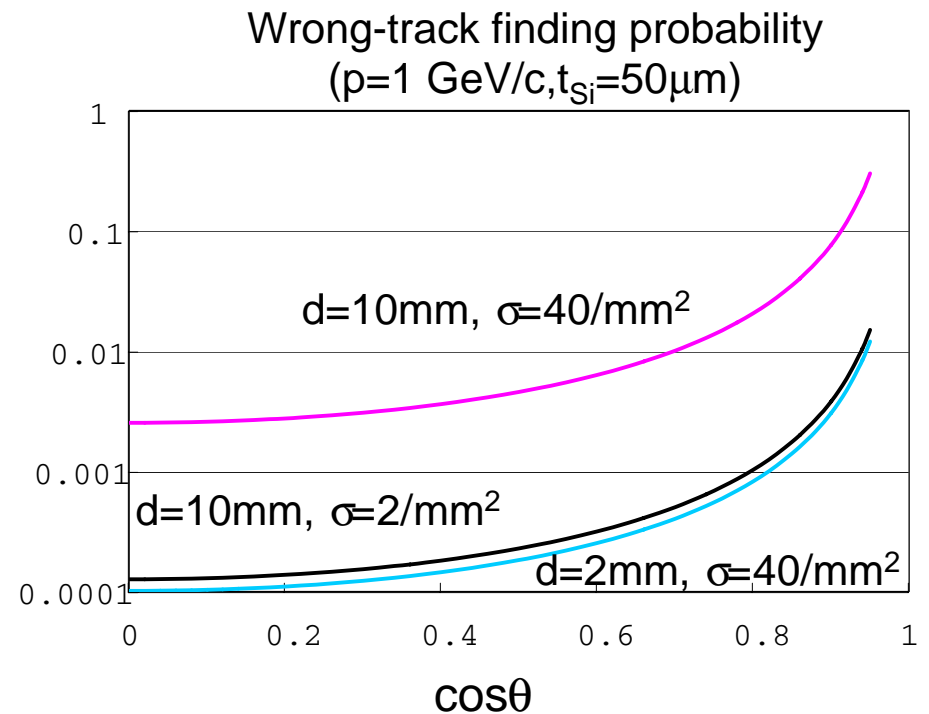
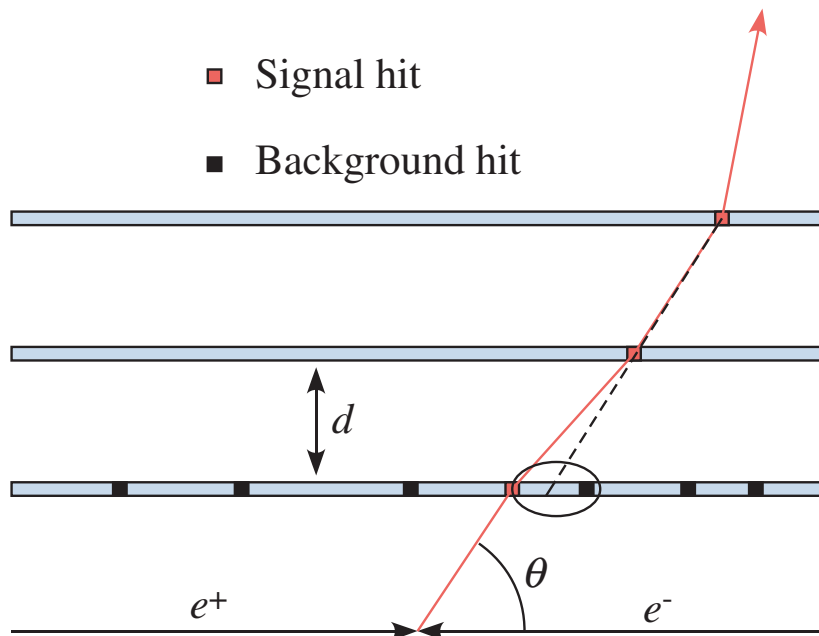
- Baseline design for GLD



Simulation study: Background rejection by cluster shape



- Disadvantage of Fine Pixel option:
 - High hit density: $\sim 40/\text{mm}^2/\text{train}$ at $R=20\text{mm}$, $B=3\text{T}$, nominal option at 500 GeV
 - Background hit can cause wrong-track finding
 - We need background rejection

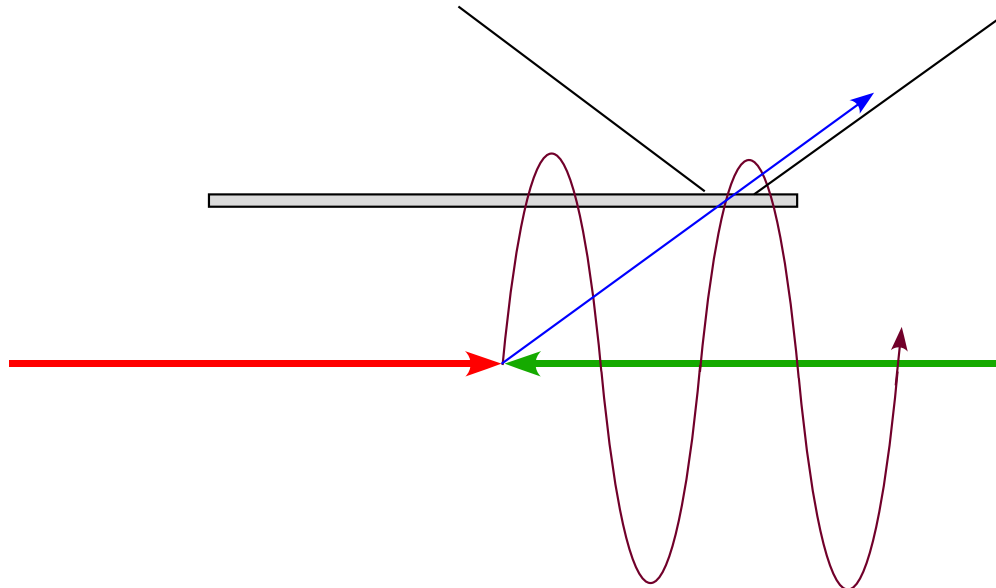
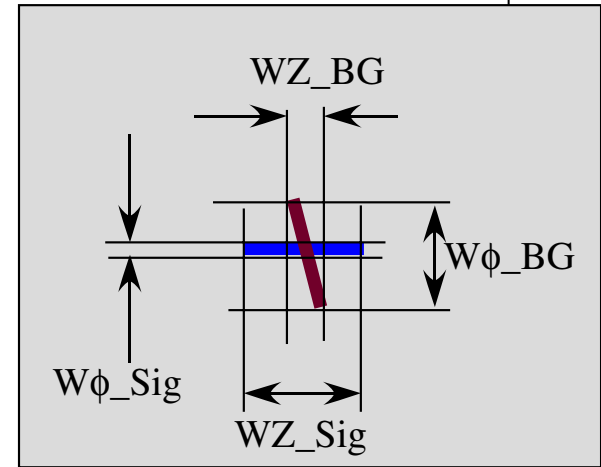




Background rejection by cluster shape

$$dW = \sqrt{(WZ_{BG} - WZ_{Sig})^2 + (W\phi_{BG} - W\phi_{Sig})^2}$$

WZ_{Sig} , $W\phi_{Sig}$: Expected width

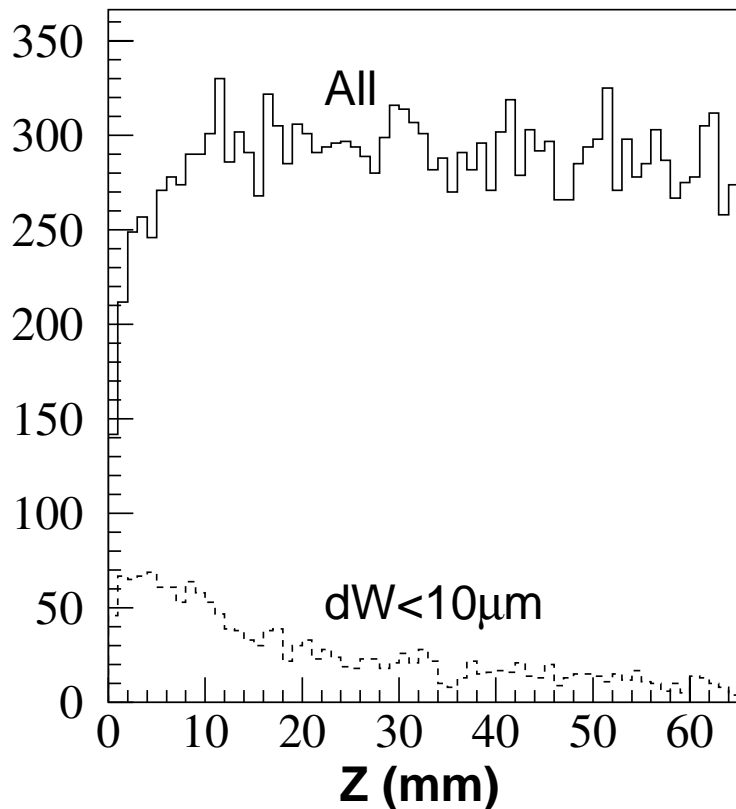




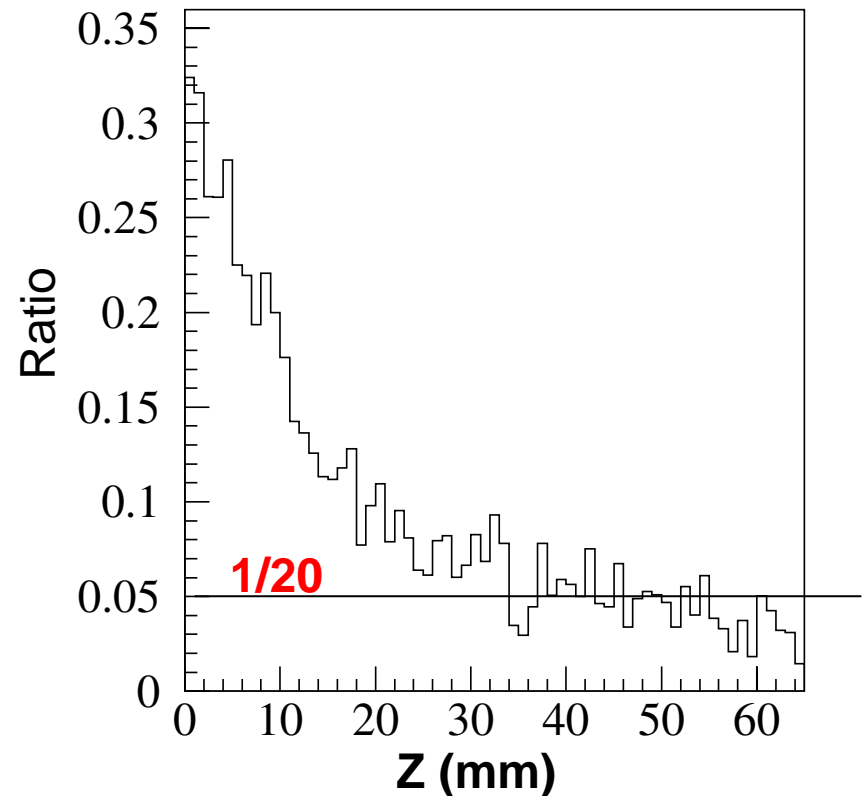
B.G. rejection by cluster shape

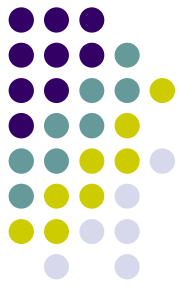
- R=20mm
- Cut at $dW=10\mu\text{m}$

Nominal 2mrad



Nominal 2mrad

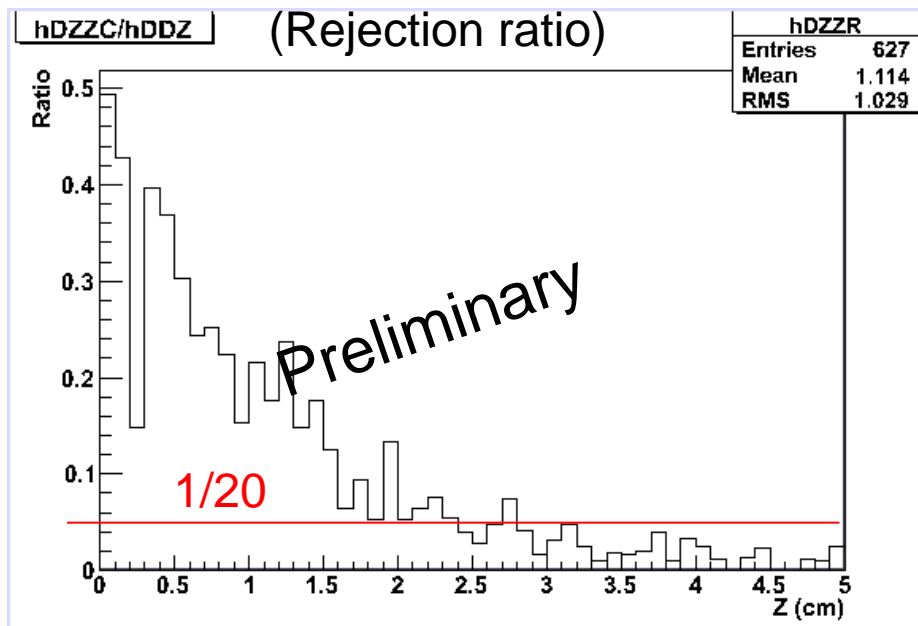




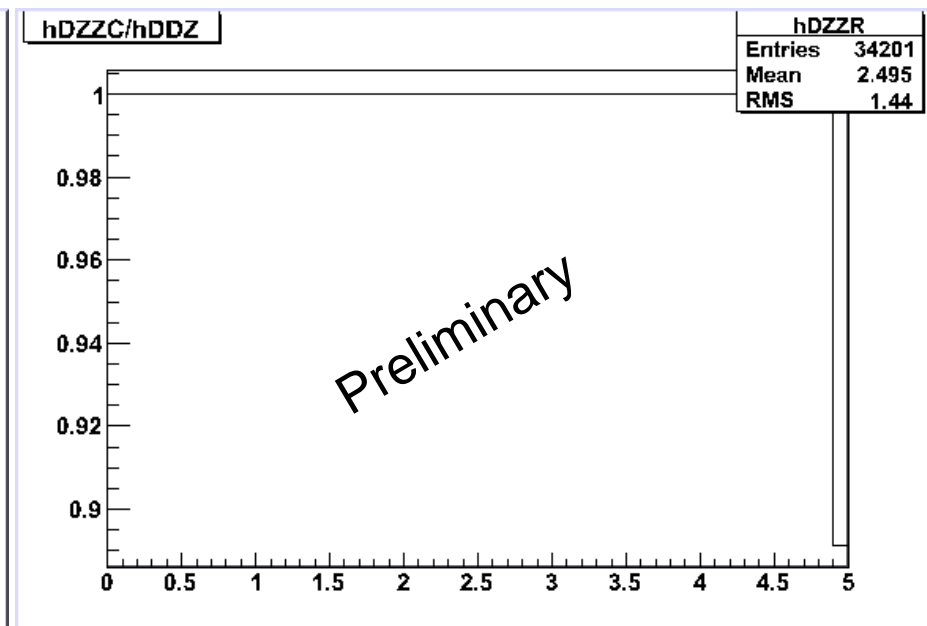
B.G. rejection by cluster shape

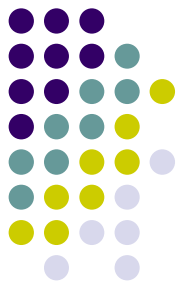
- Detector full simulation
 - $N_z > Z(\text{cm}) \times 1.2$, $N_x < 3$

Efficiency for pair b.g.



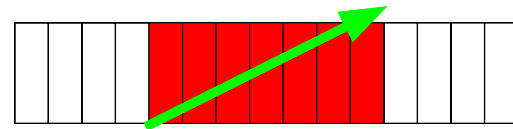
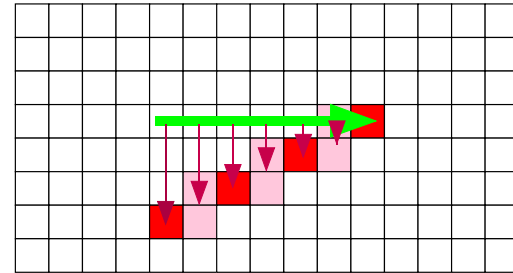
Efficiency for 1 GeV/c muon



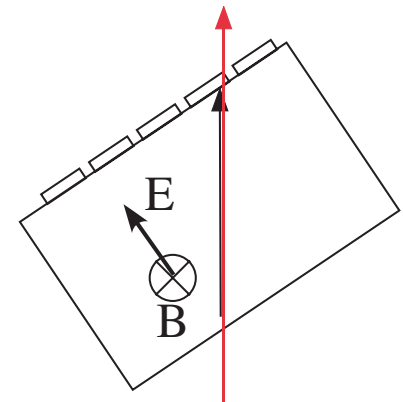
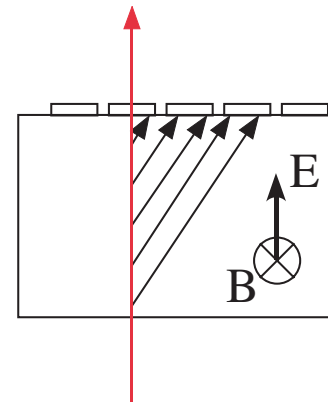


Lorentz angle in epi-layer

- Lorentz (Hall) angle in depleted-layer
 - $\tan\theta = \mu_n B$
 μ_n : electron mobility
 - Carrier velocity saturates at high E field:
 - $\mu_n = 0.07 \text{ m}^2/\text{Vs}$
 @ $T=300\text{K}$, $E=1 \times 10^4 \text{ V/cm}$
 - $\mu_n = 0.045 \text{ m}^2/\text{Vs}$
 @ $T=300\text{K}$, $E=2 \times 10^4 \text{ V/cm}$
 - Small angle can be cancelled by tilting the wafer
- May not be a serious problem
 - Number of hit pixels does not increase so much



	B=3T	B=5T
E=1x10 ⁴ V/cm	θ=12deg	θ=19deg
E=2x10 ⁴ V/cm	θ=7.7deg	θ=13deg





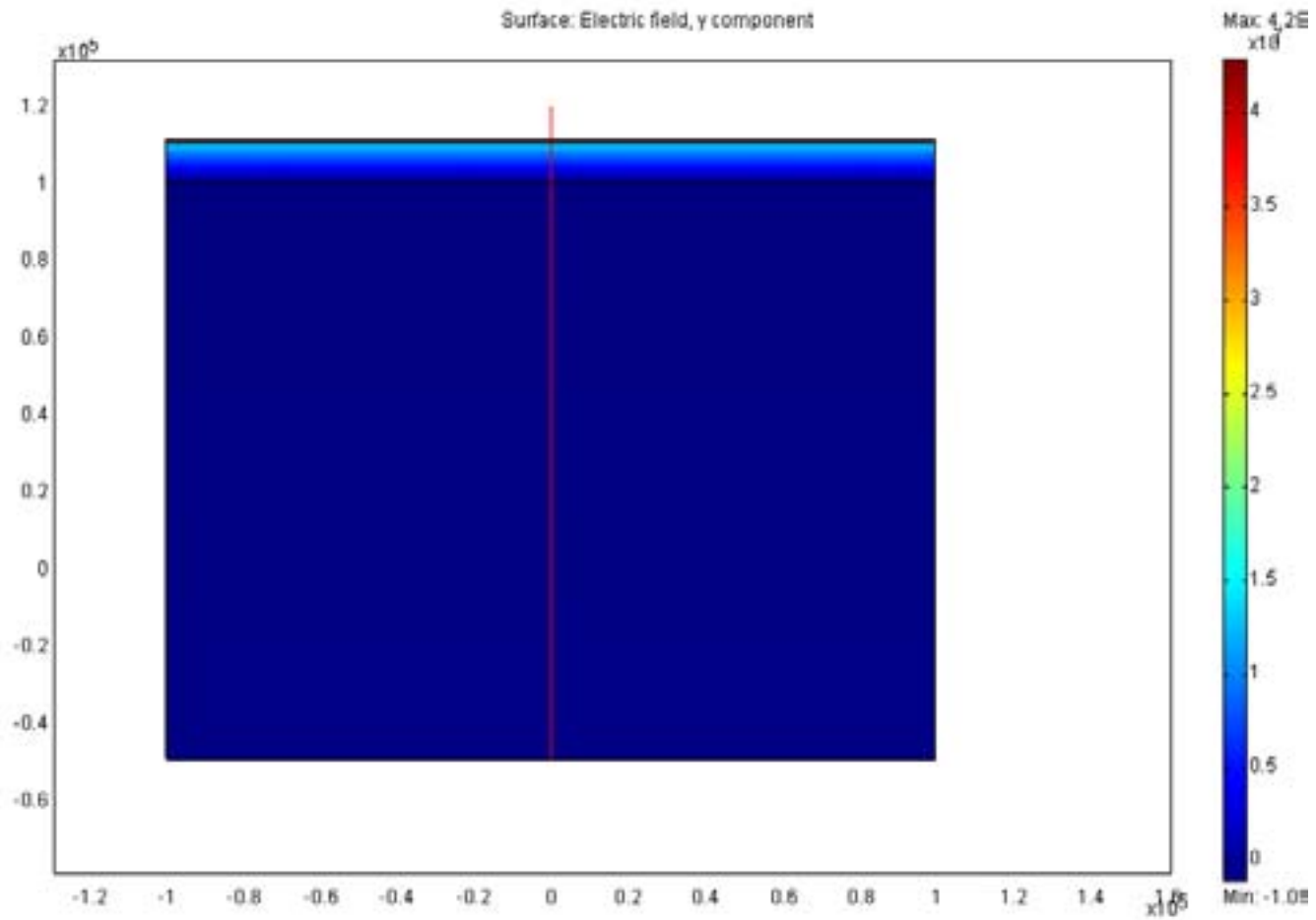
Lorentz angle

- Calculation of E-field in epi-layer
 - Tools
 - FEMLAB (COMSOL in Japan) 3.1
 - Solve Poisson equation by finite element analysis (FEA)
 - Parameters
 - Material is assumed fully depleted (No free charge)
 - n-layer: $N_D=1 \times 10^{16}/\text{cm}^3=1.6 \times 10^3 \text{ C/m}^3$
 - Epi-layer: $N_A=1 \times 10^{13}/\text{cm}^3=-1.6 \text{ C/m}^3$
 - $V_G=4 \text{ V}$
 - $t_{\text{SiO}_2}=100 \text{ nm}$
 - $t_n=1 \text{ }\mu\text{m}$
 - $t_{\text{epi}}=15 \text{ }\mu\text{m}$



Lorentz angle

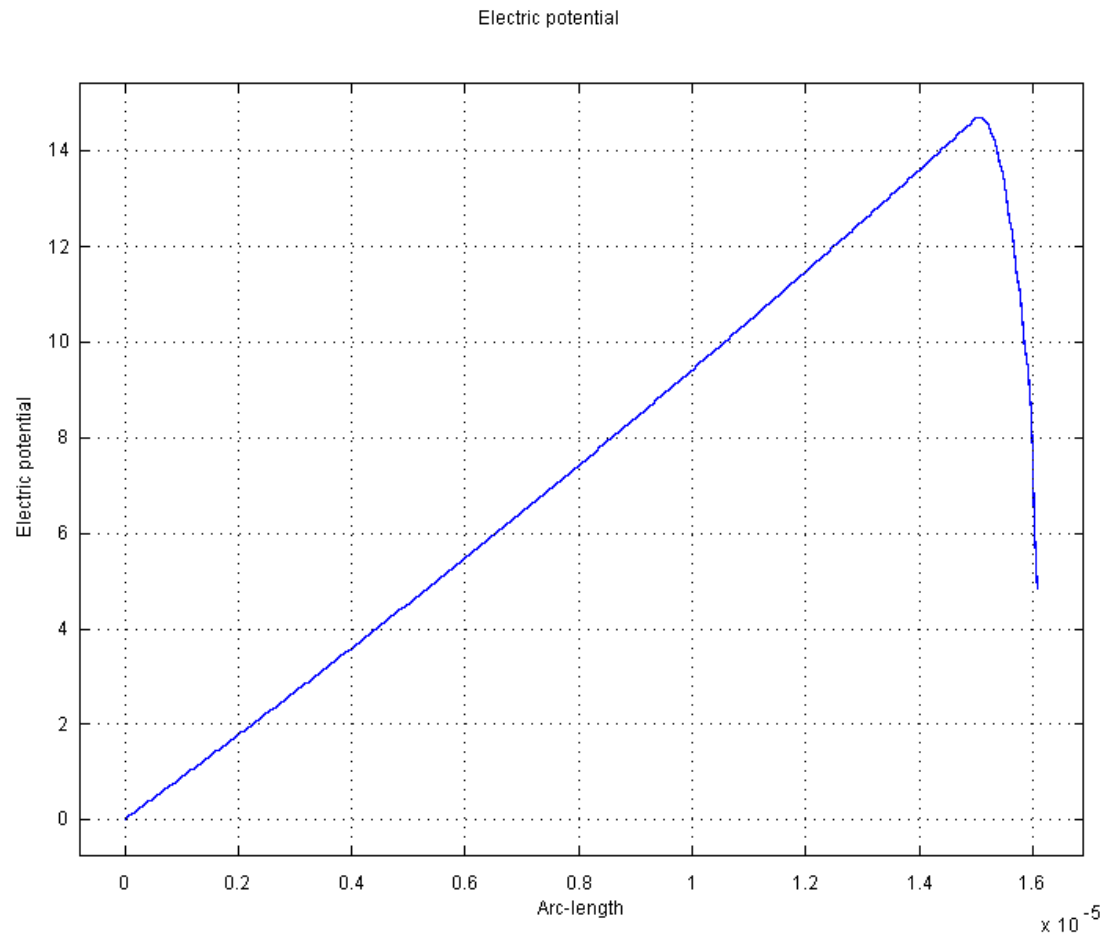
- Result of E-field calculation





Lorentz angle

- Result of E-field calculation – Potential





Lorentz angle

- Result of E-field calculation – Summary
 - Almost constant E-field of $\sim 10^4 \text{V/cm}$ in epi-layer can be achieved
 - E-field in epi-layer depends on gate voltage
 - Higher (positive) gate voltage gives higher E-field
 - Positive gate voltage should be applied during train crossing in order to get saturated carrier velocity and less Lorentz angle (Inverted (MPP) mode can be maintained for $\sim 1 \text{ms}$ at low temperature)
 - The Lorentz angle of 12 degrees is expected at $B=3\text{T}$



Status of sensor R&D

- Fully depleted CCD for astrophysics by Hamamatsu
 - 24 μm , 12 μm pixel size:
 - Available now
 - We will test them in this FY
 - 5 – 9 μm pixel size:
 - Under development
 - Will be available in 0.5 – 1 year
- Custom fully depleted FPCCD for VTX
 - High speed ($\sim 15\text{MHz}$)
 - Multi-port readout
 - We wish to start in 2006

Summary



- We propose FPCCD option for the ILC vertex detector
 - Fully depleted fine pixel ($\sim 5\mu\text{m}$) CCD
 - Accumulate hits of 1 train and read out between trains
- FPCCD has several advantages
 - Completely free from EMI
 - Moderate readout speed
 - CCD is established technology
 - No heat source in the image area
- Disadvantage of FPCCD – high background hit density – can be overcome by background rejection using hit cluster shape
- Estimated Lorentz angle in the depleted layer is small (~ 12 degrees) at 3T
- Fully depleted CCD is already available
- FPCCD for astrophysics is being developed by Hamamatsu
- We would like to start development of custom FPCCD for ILC from 2006
- Wafer thinning is essential for FPCCD option. We need R&D